

In re: Zhibo Zhang
Serial No.: 10/677,350
Filed: October 2, 2003
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In the Specification:

Page 1, lines 2-10, please amend the paragraph as follows:

This application is a divisional application of Application Serial No. 10/007,895, filed November 6, 2001, entitled *Methods of Fabricating Vertical Field Effect Transistors by Conformal Channel Layer Deposition* (now U.S. Patent [] 6,664,143), and claims the benefit of provisional Application No. 60/252,306, filed November 22, 2000, entitled *Methods of Fabricating Vertical Field Effect Transistors by Conformal Channel Layer Deposition on Sidewalls and Vertical Field Effect Transistors Fabricated Thereby*, both of which are assigned to the assignee of the present application, the disclosures of which are hereby incorporated herein by reference in their entirety as if set forth fully herein.